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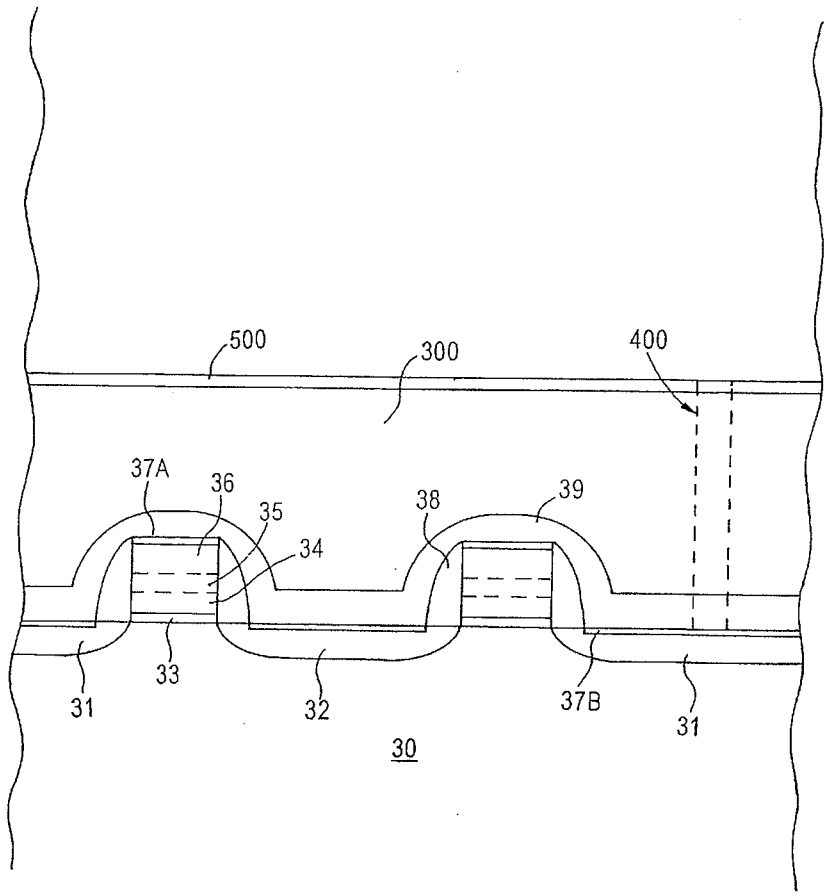
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(54) Title: PECVD SILICON-RICH OXIDE LAYER FOR REDUCED UV CHARGING

(57) Abstract: A Si-rich silicon oxide layer (500) having reduced UV transmission is deposited by PECVD, on an interlayer dielectric (300), prior to metallization, thereby reducing V_t. Embodiments include depositing a UV opaque Si-rich silicon oxide layer (500) having an R.I. of 1.7 to 2.0.



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